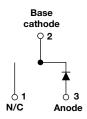


HEXFRED®, Ultrafast Soft Recovery Diode, 8 A



TO-263AB (D²PAK)



PRODUCT SUMMARY								
Package	TO-263AB (D ² PAK)							
I _{F(AV)}	8 A							
V_{R}	1200 V							
V _F at I _F	2.4 V							
t _{rr} (typ.)	28 ns							
T _J max.	150 °C							
Diode variation	Single die							

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- · Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA08TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V_R		1200	V					
Maximum continuous forward current	I _F	T _C = 100 °C	8						
Single pulse forward current	I _{FSM}		130	Α					
Maximum repetitive forward current	I _{FRM}		32						
Maximum nawar discination	В	T _C = 25 °C	73.5	W					
Maximum power dissipation	P_{D}	T _C = 100 °C	29	VV					
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C					

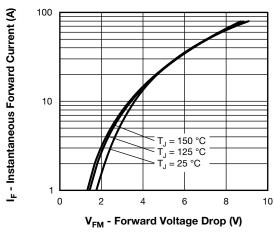


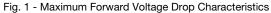


ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V_{BR}	Ι _R = 100 μΑ	1200	-	-				
Maximum forward voltage	V_{FM}	I _F = 8.0 A	-	2.6	3.3	V			
		I _F = 16 A -		3.4	4.3				
		I _F = 8.0 A, T _J = 125 °C	-	2.4	3.1				
Maximum reverse		$V_R = V_R$ rated	-	0.31	10				
leakage current		$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} V_R \text{rated}$	-	135	1000	μΑ			
Junction capacitance	C _T	V _R = 200 V	-	11	20	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	_F = 1.0 A, dl _F /dt = 200 A/µs, V _R = 30 V			-			
	t _{rr1}	T _J = 25 °C		-	63	95	ns		
	t _{rr2}	T _J = 125 °C		-	106	160			
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.5	8.0	A nC A/μs		
	I _{RRM2}	T _J = 125 °C	$I_F = 8.0 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$	-	6.2	11			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	$V_{\rm R} = 200 \text{ V}$	-	140	380			
Reverse recovery charge	Q _{rr2}	T _J = 125 °C] "	-	335	880			
Peak rate of fall of recovery current during t _b	dI _{(rec)M} /dt1	T _J = 25 °C		-	133	- 1			
	dI _{(rec)M} /dt2	T _J = 125 °C		-	85	-			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	1.7	K/W			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	N/W			
Weight			-	2.0	-	g			
vveigni			-	0.07	1	OZ.			
Marking device		Case style TO-263AB (D ² PAK)		HFA08	ΓB120S	•			





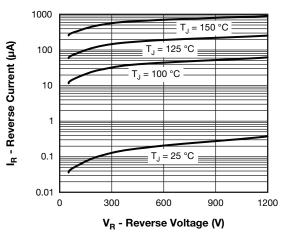


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

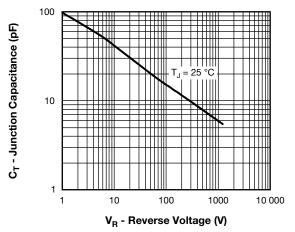


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

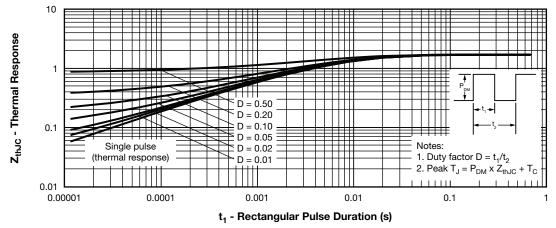


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





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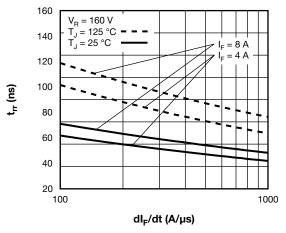


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

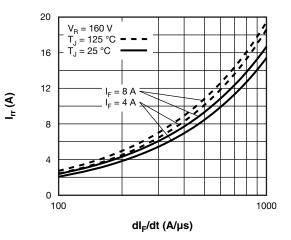


Fig. 6 - Typical Recovery Current vs. dl_F/dt

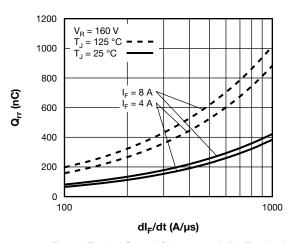


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

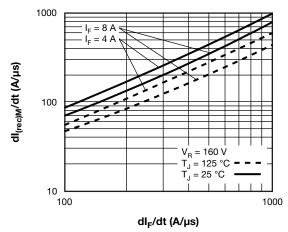


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

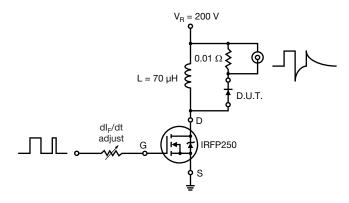
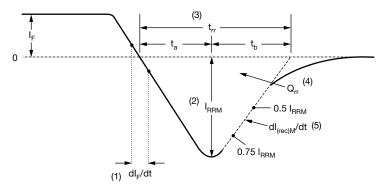


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

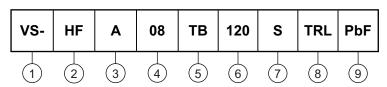
(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 HEXFRED® family
- Process designator: A = electron irradiated
- 4 Current rating (08 = 8 A)
- 5 Package outline (TB = TO-220, 2 leads)
- Voltage rating (120 = 1200 V)
- S = D²PAK
- 8 • None = tube
 - TRL = tape and reel (left oriented)
 - TRR = tape and reel (right oriented)
- PbF = lead (Pb)-free, for tube packaged
 - P = lead (Pb)-free, for tape and reel packaged

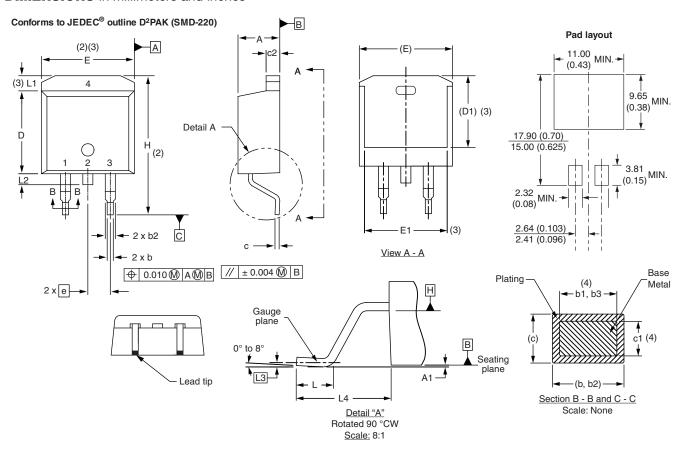
LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?95046</u>						
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA08TB120SPBF	50	1000	Antistatic plastic tube						
VS-HFA08TB120STRRP	800	800	13" diameter reel						
VS-HFA08TB120STRLP	800	800	13" diameter reel						



D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	e 2.54 BSC 0.100 BSC		BSC				
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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